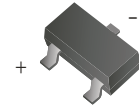


## CDST19-G/20-G

High Speed  
RoHS Device



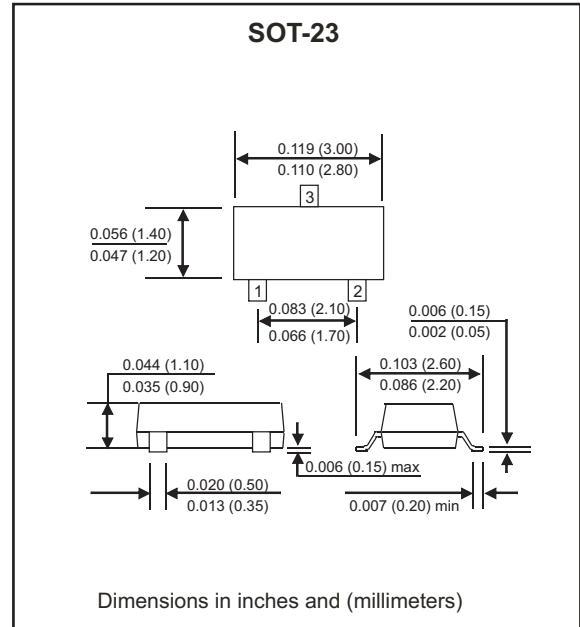
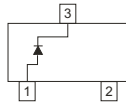
### Features

- Fast switching diode.
- Surface mount package ideally for automatic insertion.
- For general purpose switching applications.
- High conductance.

### Mechanical data

- Case: SOT-23
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.
- Weight: 0.008 gram.
- Marking: CDST19-G JP  
CDST20-G JR

### Circuit Diagram



### Maximum Rating (at Ta=25°C unless otherwise noted)

Parameter	Symbol	CDST19-G	CDST20-G	Unit
Non-Repetitive peak reverse voltage	$V_{RM}$	100	150	V
DC blocking voltage	$V_R$	100	150	V
Average rectified output current	$I_o$	200		mA
Power dissipation	$P_D$	250		mW
Thermal resistance-Junction to ambient air	$R_{\theta JA}$	500		°C/W
Junction temperature	$T_J$	150		°C
Storage temperature range	$T_{STG}$	-65 ~ +150		°C

### Electrical Characteristics (at TA=25 °C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{BR}$	$I_R=100\mu A$	100 150		V
Reverse leakage current	$I_R$	$V_R=100V$ $V_R=150V$		0.1	UA
Forward voltage	$V_F$	$I_F=100mA$ $I_F=200mA$		1 1.25	V
Junction capacitance	$C_J$	$V_R=0V, f=1MHz$		5	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=30mA, I_{rr}=0.1 \times I_R$		50	nS

## Characteristic Curves (CDST19-G/20-G)

Fig.1 - Forward Characteristics

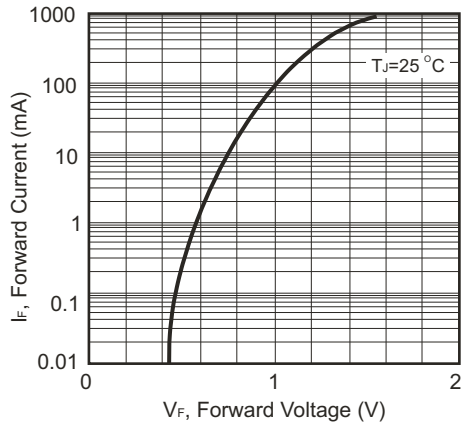


Fig.2 - Leakage Current vs Junction Temperature

